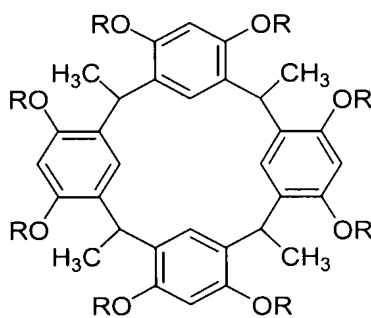


IN THE CLAIMS

Please amend the claims as follows:

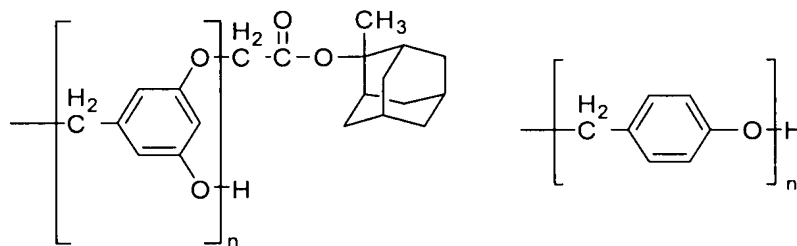
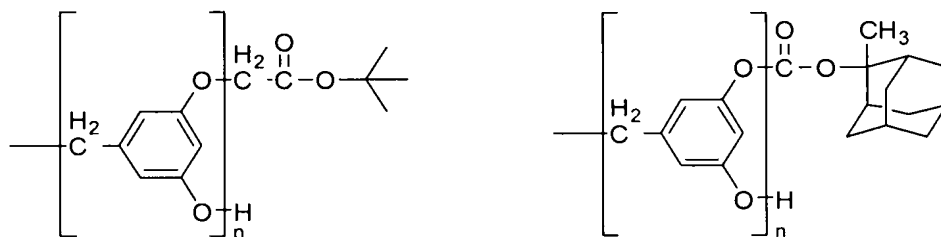
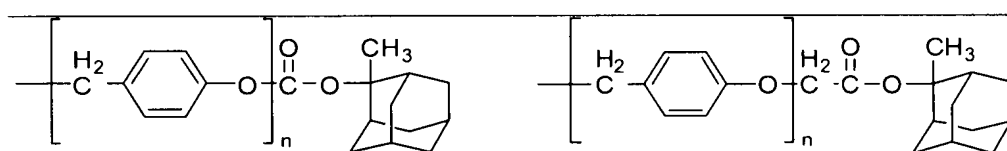
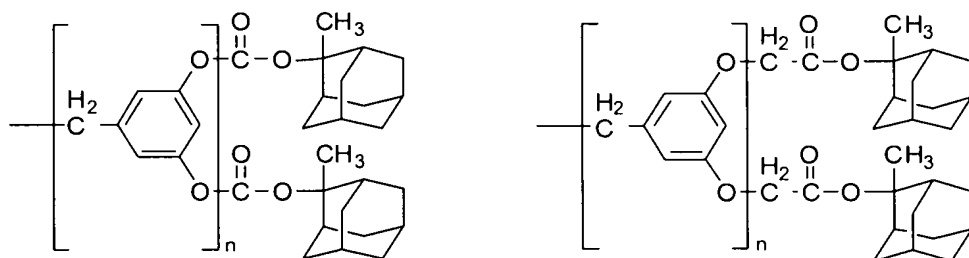
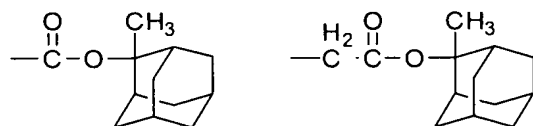
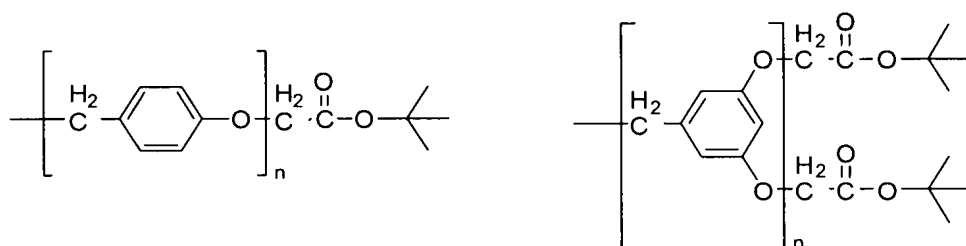
Claims 1-17 (Canceled).

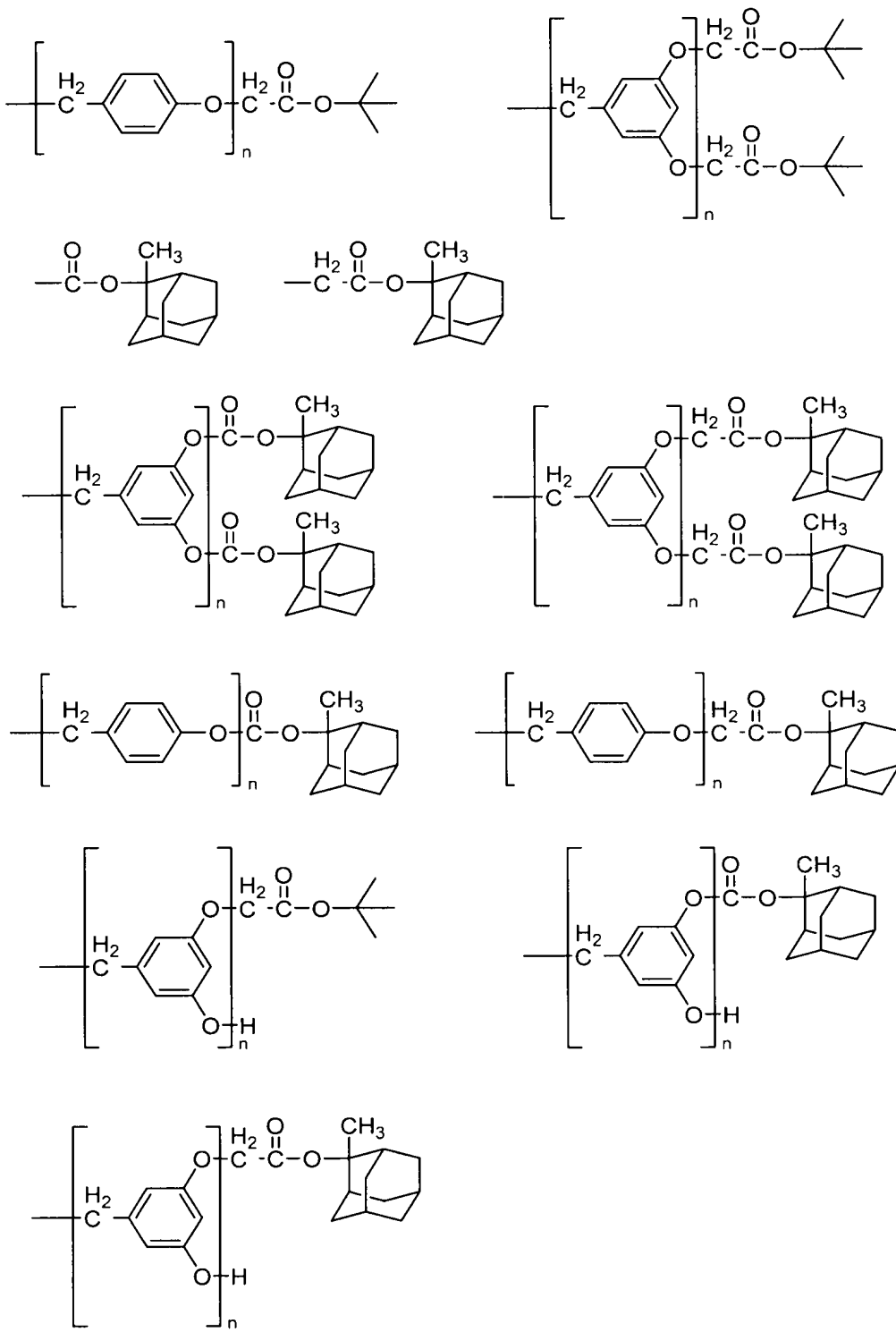
Claim 18 (Currently Amended): A calixresorcinarene compound shown by formula
(1),



(1)

wherein R individually represents a hydrogen atom, a 1-tetrahydropyranyl group, a 1-tetrahydrofuranyl group, or one or more organic groups selected from the group consisting of the organic groups shown by the following formulas,





wherein n individually represents an integer of 1 to 50,

provided that a compound in which R is selected only from a hydrogen atom, a 1-tetrahydropyranyl group and a 1-tetrahydrofuran group is excluded.

Claim 19 (Previously Presented): A method for the purification of a calixresorcinarene compound according to claim 18 comprising washing said compound with an acidic aqueous solution and processing the washed compound with an ion-exchange resin.

Claim 20 (Previously Presented): A photoresist base material for extreme ultraviolet radiation and/or an electron beam comprising the calixresorcinarene compound according to claim 18 and shown by formula (1).

Claim 21 (Previously Presented): A photoresist composition for extreme ultraviolet radiation and/or an electron beam comprising the photoresist base material according to claim 20 and a solvent.

Claim 22 (Previously Presented): The photoresist composition according to claim 21, further comprising a photoacid generator.

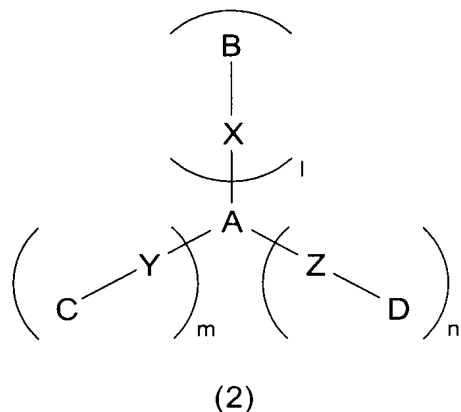
Claim 23 (Previously Presented): The photoresist composition according to claim 21, further comprising a basic organic compound as a quenching agent.

Claims 24-32 (Cancelled).

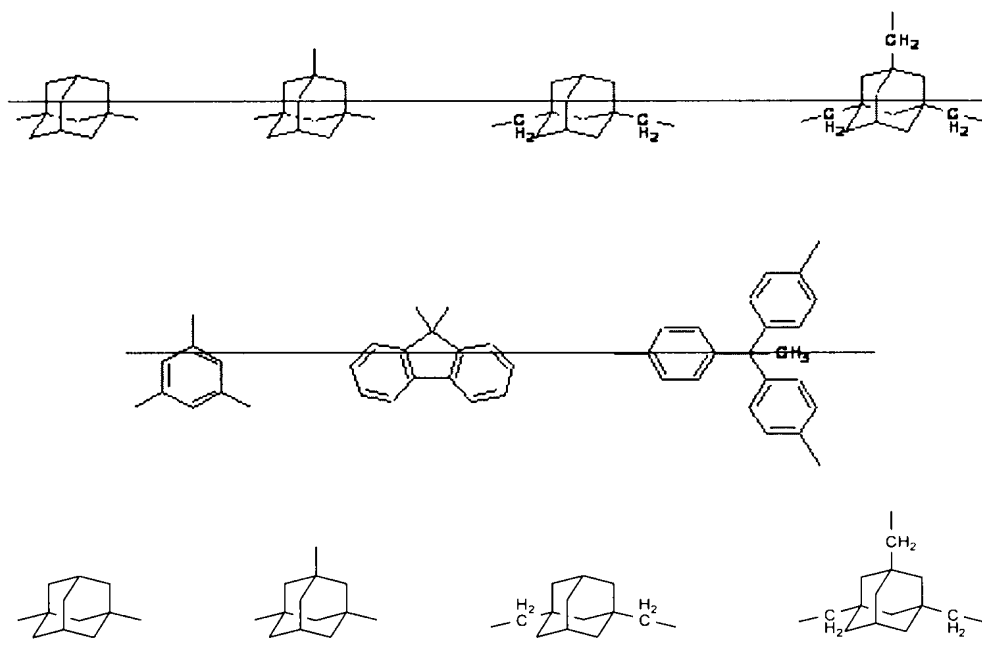
Claim 33 (Previously Presented): A method for microfabrication by lithography using the photoresist composition according to claim 21.

Claim 34 (Previously Presented): A semiconductor device prepared using the photoresist composition according to claim 21.

Claim 35 (Currently Amended): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,

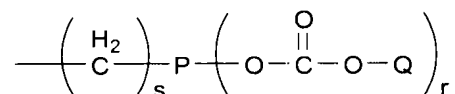


wherein A is an organic group represented by any of the following formulas,



B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butylloxycarbonylmethyl group, tert-butylloxycarbonyl group, 1-tetrahydropyranyl group, 1-

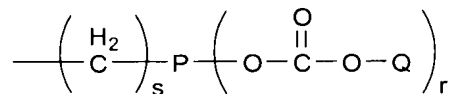
tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, an organic group shown by the formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10,

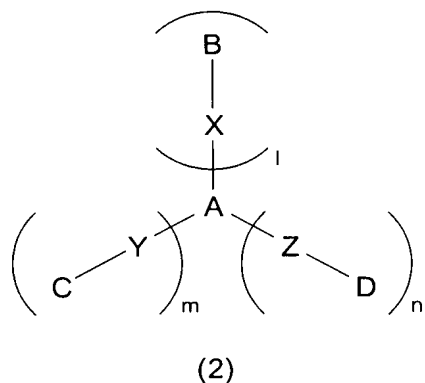
X, Y, and Z individually represent a single bond or an ether bond, and

l + m + n = 2 or 3.

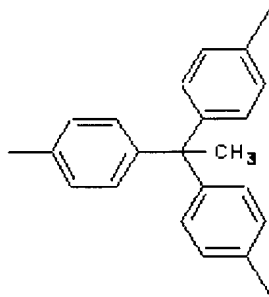
Claim 36 (Previously Presented): The photoresist composition according to claim 35, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

Claim 37 (Cancelled).

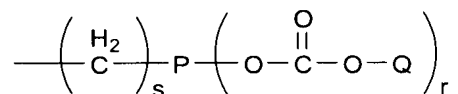
Claim 38 (Currently Amended): A photoresist composition comprising a photoresist base material that is a radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by the following formula,



B, C, and D are individually a ~~tert-butylloxycarbonylmethyl group~~, tert-butylloxycarbonyl group, or an organic group shown by formula,

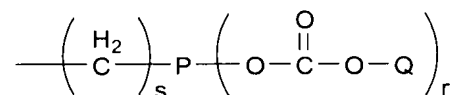


wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10,

X, Y, and Z individually represent a single bond or an ether bond, and

$$l + m + n = 3.$$

Claim 39 (Previously Presented): The photoresist composition according to claim 38, wherein the organic group shown by the following formula,



is a 4-(tert-butoxycarbonyloxy)benzyl group or a 3,5-di(tert-butoxycarbonyloxy)benzyl group.

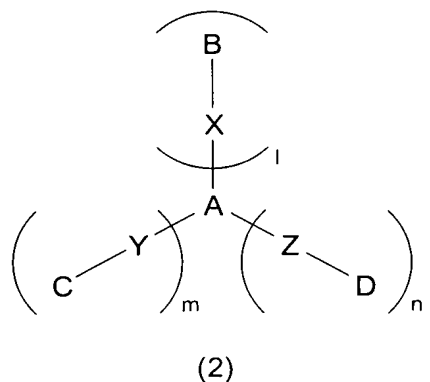
Claim 40 (Previously Presented): The photoresist composition according to claim 38, wherein the radiation is extreme ultraviolet radiation or an electron beam.

Claim 41 (Previously Presented): The photoresist composition according to claim 35, wherein at least one of B, C, and D is a hydrogen atom and X, Y, and Z are ether bonds.

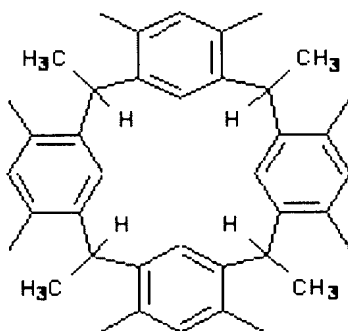
Claim 42 (Previously Presented): The photoresist composition according to claim 35, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.

Claim 43 (Previously Presented): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by

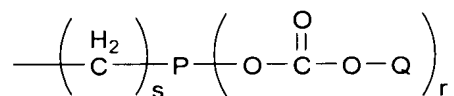
formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by the following formula,



B, C, and D are individually an organic group shown by formula,

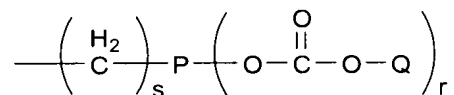


wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl

group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



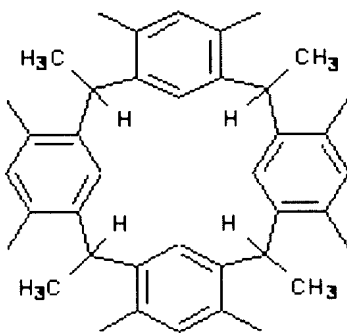
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10,

X, Y, and Z individually represent a single bond or an ether bond, and

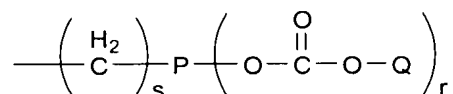
$$1 + m + n = 8.$$

Claim 44 (Previously Presented): The photoresist composition according to claim 43, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

Claim 45 (Previously Presented): The photoresist composition according to claim 43, wherein A is the organic group represented by the following formula,



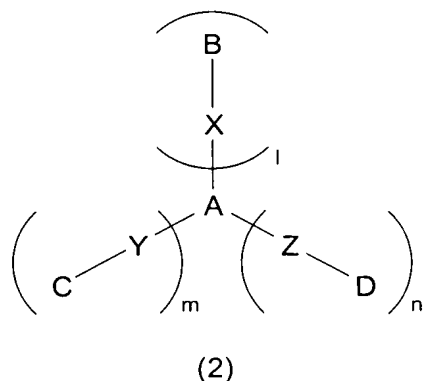
B, C, and D are individually an organic group shown by the following formula,



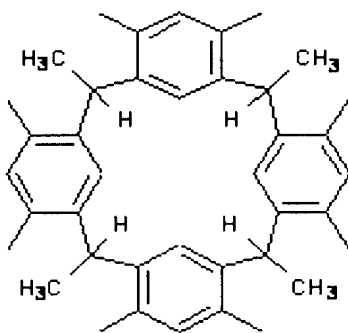
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1),
 Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is
 an integer of 0 to 10, and

X, Y, and Z are ether bonds.

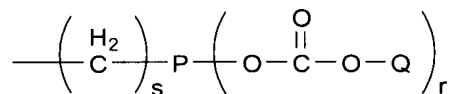
Claim 46 (Previously Presented): A photoresist composition comprising a photoresist
 base material that is a radiation-reactive organic compound shown by formula (2), obtained
 by washing with an acidic aqueous solution and processing with an ion-exchange resin, a
 photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by the following formula,



B, C, and D are individually an organic group shown by formula,

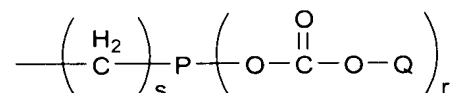


wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10,

X, Y, and Z individually represent a single bond or an ether bond, and

$$l + m + n = 8.$$

Claim 47 (Previously Presented): The photoresist composition according to claim 46, wherein the organic group shown by the following formula,

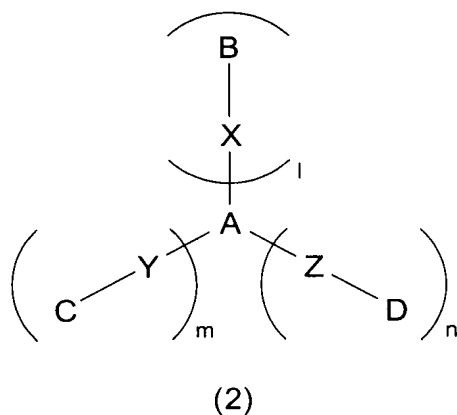


is a 4-(tert-butoxycarbonyloxy)benzyl group or a 3,5-di(tert-butoxycarbonyloxy)benzyl group.

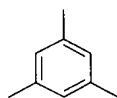
Claim 48 (Previously Presented): The photoresist composition according to claim 46, wherein the radiation is extreme ultraviolet radiation or an electron beam.

Claim 49 (Previously Presented): The photoresist composition according to claim 46, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.

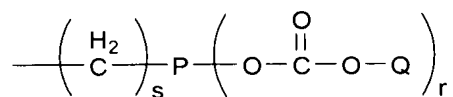
Claim 50 (New): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by the following formula,



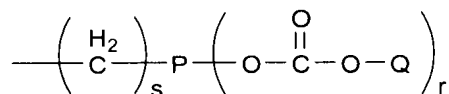
B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, an organic group shown by the formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of $(r + 1)$, Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

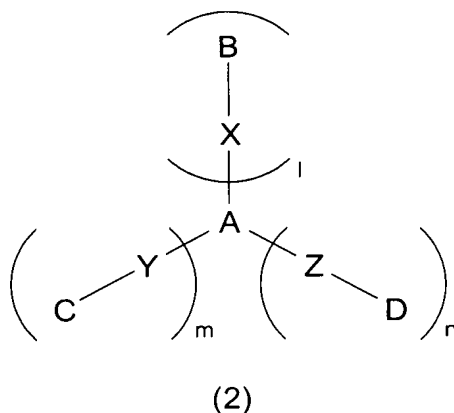
X, Y, and Z individually represent a single bond or an ether bond, and $l + m + n = 2$ or 3.

Claim 51 (New): The photoresist composition according to claim 50, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

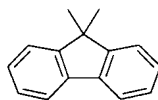
Claim 52 (New): The photoresist composition according to claim 50, wherein at least one of B, C, and D is a hydrogen atom and X, Y, and Z are ether bonds.

Claim 53 (New): The photoresist composition according to claim 50, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.

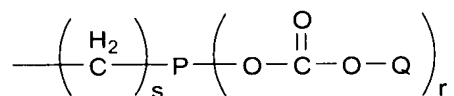
Claim 54 (New): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



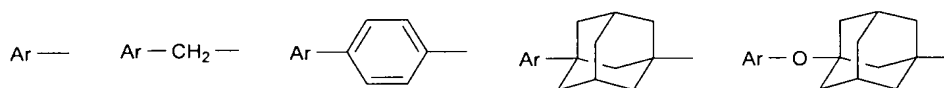
wherein A is an organic group represented by the following formula,



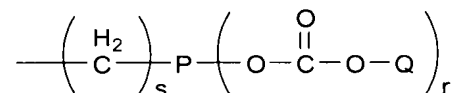
B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, an organic group shown by the formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

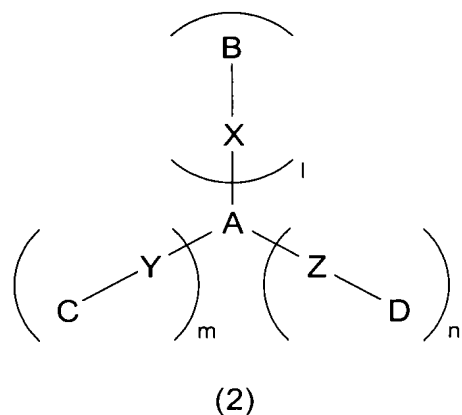
X, Y, and Z individually represent a single bond or an ether bond, and l + m + n = 2 or 3.

Claim 55 (New): The photoresist composition according to claim 54, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

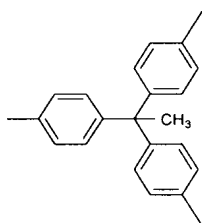
Claim 56 (New): The photoresist composition according to claim 54, wherein at least one of B, C, and D is a hydrogen atom and X, Y, and Z are ether bonds.

Claim 57 (New): The photoresist composition according to claim 54, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.

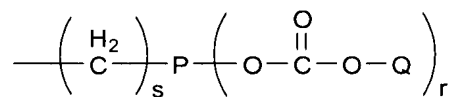
Claim 58 (New): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



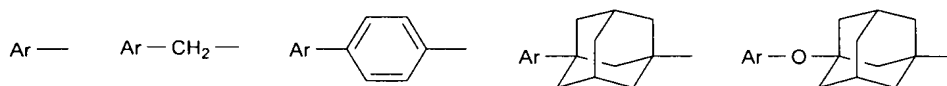
wherein A is an organic group represented by the following formula,



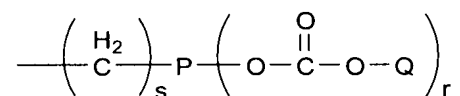
B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, an organic group shown by the formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

X, Y, and Z individually represent a single bond or an ether bond, and l + m + n = 2 or 3.

Claim 59 (New): The photoresist composition according to claim 58, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

Claim 60 (New): The photoresist composition according to claim 58, wherein at least one of B, C, and D is a hydrogen atom and X, Y, and Z are ether bonds.

Claim 61 (New): The photoresist composition according to claim 58, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.